

Features

- · Integrated LNA, Mixer and LO Buffer Amplifier
- 1.8 dB Noise Figure
- 13 dB Conversion Gain
- Lead-Free 4 mm 24-lead QFN Package
- 100% RF, DC and NF Testing
- RoHS* Compliant and 260°C Reflow Compatible

Description

The XR1011-QH is a 4.5 - 10.5 GHz QFN packaged receiver that has a noise figure of 1.8 dB and 13 dB conversion gain across the band. The device integrates an LNA, image reject mixer and LO buffer amplifier within a fully molded 4 mm QFN package. The image reject mixer eliminates the need for a band pass filter after the LNA to remove thermal noise at the image frequency. I and Q mixer outputs are provided and an external 90° hybrid is required to select the desired sideband. This device uses MACOM device model technology, and is based upon electron beam lithography to ensure high repeatability and uniformity.

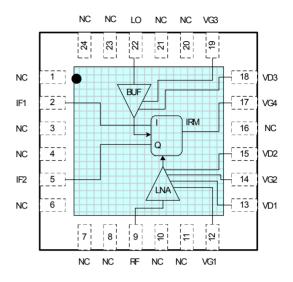
This device is specifically designed for Point to Point radio applications and is well suited for other telecom applications such as SATCOM and VSAT.

Ordering Information¹

| Part Number | Package |
|----------------|-------------------|
| XR1011-QH-0GP0 | bulk quantity |
| XR1011-QH-0GPT | tape and reel |
| XR1011-QH-EV1 | evaluation module |

^{1.} Reference Application Note M513 for reel size information.

Functional Schematic



Pin Configuration^{2,3}

| Pin# | Pin Name | Function |
|--|----------|---------------|
| 2 | IF1 | IF1 Output |
| 5 | IF2 | IF2 Output |
| 9 | RF | RF Input |
| 12 | VG1 | Gate 1 Bias |
| 13 | VD1 | Drain 1 Bias |
| 14 | VG2 | Gate 2 Bias |
| 15 | VD2 | Drain 2 Bias |
| 17 | VG4 | Gate 4 Bias |
| 18 | VD3 | Drain 3 Bias |
| 19 | VG3 | Gate 3 Bias |
| 22 | LO | LO Input |
| 1,3,4,6,7,8, 10,11,16,20, 21,23,24 | NC | Not Connected |

^{2.} The exposed pad centered on the package bottom must be connected to RF and DC ground.

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^{3.} It is recommended to externally ground all N/C pins.

^{*} Restrictions on Hazardous Substances, European Union Directive 2011/65/EU.



Receiver 4.5 - 10.5 GHz

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Electrical Specifications: RF/LO Frequency = 4.5 - 10.5 GHz, T_A = +25°C

| Parameter | Units | Min. | Тур. | Max. |
|----------------------------------|-------|------|------|------|
| IF Frequency Range | GHz | DC | _ | 3.5 |
| Conversion Gain | dB | 12 | 13 | 15 |
| Noise Figure | dB | _ | 1.8 | _ |
| Input Third Order Intercept | dBm | _ | +3 | _ |
| Image Rejection | dBc | 15 | 20 | _ |
| LO Input Drive | dBm | _ | +5 | _ |
| LO/RF Isolation | dB | _ | -50 | _ |
| RF Input Return Loss | dB | _ | 10 | _ |
| LO Input Return Loss | dB | _ | 10 | _ |
| IF Return Loss | dB | _ | 10 | _ |
| Drain Bias Voltage 1,2,3 | VDC | _ | +4 | +4 |
| Gate Bias Voltage 1,2,34 | VDC | -1.2 | -0.3 | 0.2 |
| Gate Bias Voltage 4 ⁵ | VDC | _ | -2 | _ |
| Supply Current 1 | mA | _ | 25 | _ |
| Supply Current 2 | mA | _ | 45 | _ |
| Supply Current 3 | mA | _ | 60 | _ |
| Supply Current 4 | mA | _ | 2 | _ |

^{4.} V_G1,2 and 3 are adjusted to achieve constant drain current regulation.

Absolute Maximum Ratings 6,7

| Parameter | Absolute Max. |
|-----------------------|---------------------|
| Supply Voltage | +4.3 V |
| Supply Current | 180 mA |
| Gate Bias Voltage | -3 V |
| Power Dissipation | 750 mW |
| RF Input Power | +14 dBm |
| LO Input Power | +15 dBm |
| Operating Temperature | -55°C to +85°C |
| Storage Temperature | -65°C to +150°C |
| Channel Temperature | -40°C to MTTF Graph |
| MSL Level | MSL3 |

^{6.} Operation of this device above any one of these parameters may cause permanent damage.

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

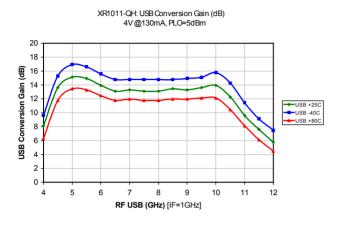
Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these HBM Class 1A, MM Class A devices.

^{5.} V_G4 provides mixer bias and is fixed at -2 V.

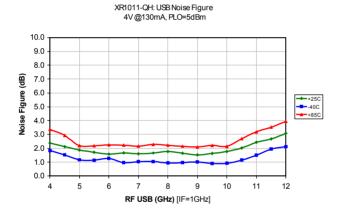
Channel temperature directly affects a device's MTTF. Channel temperature should be kept as low as possible to maximize lifetime.

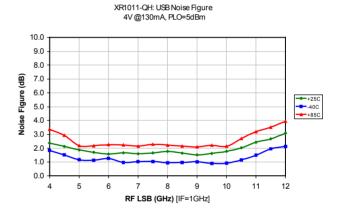


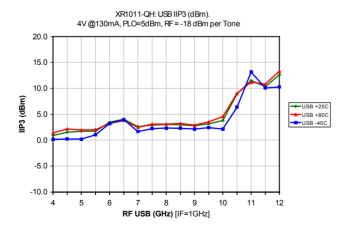
Typical Performance Curves

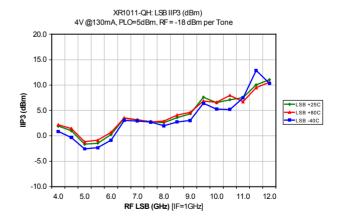












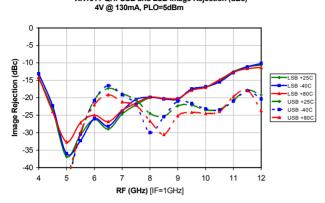


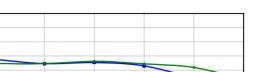
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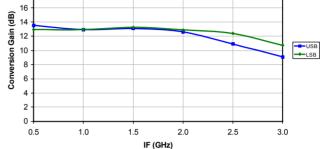
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Typical Performance Curves

XR1011-QH: USB and LSB Image Rejection (dBc)

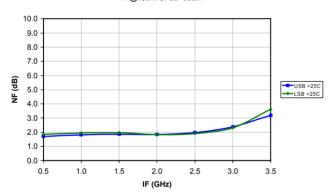




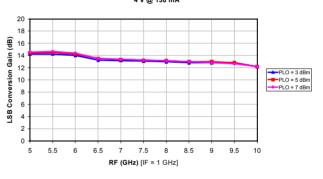


XR1011-QH: Conversion Gain (dB) vs IF (GHz) at LO=7.5 GHz 4V @130mA, PLO=5dBm

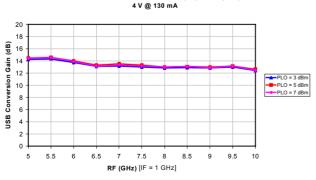
XR1011-QH: Noise Figure (dB) vs IF (GHz) at LO=7.5 GHz 4V @130mA, PLO=5dBm



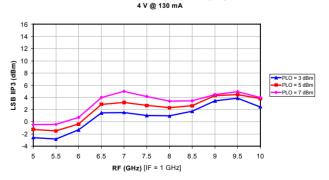
XR1011-QH: LSB Conversion Gain (dB) vs. RF (GHz). 4 V @ 130 mA



XR1011-QH: USB Conversion Gain (dB) vs. RF (GHz).



XR1011-QH: LSB IIP3 (dBm) vs. RF (GHz).

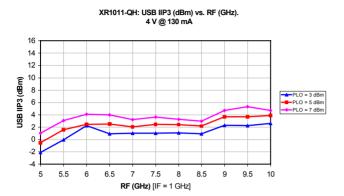


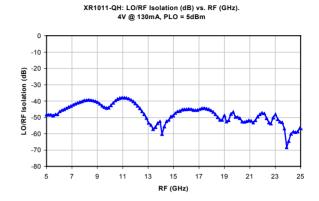


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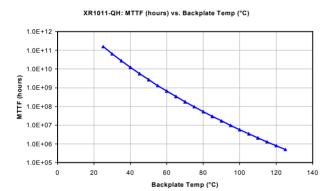
Typical Performance Curves





MTTF

MTTF is calculated from accelerated life-time data of single devices and assumes an isothermal back-plate.



MxN Spurious Outputs

| | | nLO | | | | |
|-----|---|------|------|-----|----|----|
| | | 0 | 1 | 2 | 3 | 4 |
| | 0 | - | 33 | 38 | 49 | 61 |
| | 1 | 30 | 0 | 71 | 74 | - |
| mRF | 2 | 66 | 65 | 17 | 80 | 72 |
| | 3 | 97 | 105 | 79 | 30 | 79 |
| | 4 | >110 | >110 | 108 | 88 | 45 |

RF=7.5GHz @-10dBm LO=6.5GHz @+5dBm Data measured without 90deg hybrid All values in dBc below IF power level

LO Harmonics

| LO Freq | nLO Spur, RF Port | | | |
|---------|-------------------|-----|----|----|
| (GHz) | 1 | 2 | 3 | 4 |
| 4 | 53 | 70 | 70 | 88 |
| 5 | 57 | 71 | 79 | 64 |
| 6 | 54 | 66 | 67 | 64 |
| 7 | 50 | 102 | 61 | 81 |
| 8 | 49 | 74 | 61 | 67 |
| 9 | 51 | 54 | 71 | 70 |
| 10 | 50 | 45 | 72 | 80 |
| 11 | 48 | 40 | 62 | 64 |
| 12 | 53 | 42 | 64 | 48 |

LO = +5 dBm

Values in dBc relative to LO input level, measured at RF IN port



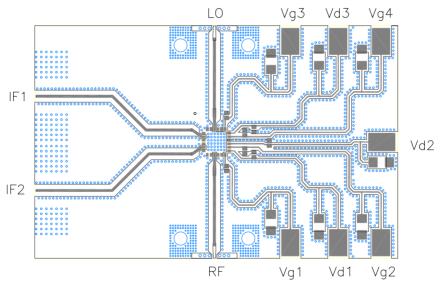
App Note [1] Biasing -

As shown in the Pin Designations table, the device is operated by biasing VD1,2,3 at 4 V with 25, 45, 60 mA respectively. Additionally, a fixed voltage bias of -2 V is required for mixer bias. It is recommended to use active bias to keep the currents constant in order to maintain the best performance over temperature. Depending on the supply voltage available and the power dissipation constraints, the bias circuit may be a single transistor or a low power operational amplifier, with a low value resistor in series with the drain supply used to sense the current. The gate is controlled to maintain correct drain current and thus drain voltage. The typical gate voltage needed to do this is -0.3 V. Make sure to sequence the applied voltage to ensure negative gate bias is available before applying the positive drain supply.

App Note [2] Board Layout -

As shown in the board layout, it is recommended to provide 100 pF decoupling caps as close to the bias pins as possible, with additional 10 µF decoupling caps.

Recommended Board Layout



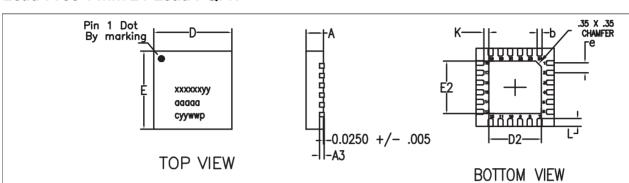
Recommended Decoupling Capacitors: 100pF 0402, $10\mu F$ 0805 Recommend to externally ground all N/C pins



Receiver 4.5 - 10.5 GHz

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Lead-Free 4 mm 24-Lead PQFN[†]

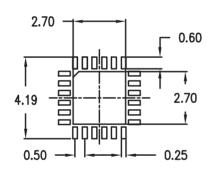


MARKINGS: PIN 1/BOM REV/Pb FREE SYM MIMOX PART/MODEL NO. WAFER LOT NUMBER DATE CODE

NOTES:

1. DIMENSIONS ARE IN MM.

RECOMMENDED SOLDER PAD PITCH AND DIMENSIONS



| | MIN | TYP | MAX | | |
|----|----------|----------|------|--|--|
| Α | 0.80 | 0.90 | 1.00 | | |
| A3 | | 0.20 REF | | | |
| b | 0.20 | 0.25 | 0.30 | | |
| K | 0.20 | _ | _ | | |
| D | 4.00 BSC | | | | |
| E | 4.00 BSC | | | | |
| е | 0.50 | | | | |
| D2 | 2.45 | 2.60 | 2.75 | | |
| E2 | 2.45 | 2.60 | 2.75 | | |
| L | 0.20 | 0.30 | 0.40 | | |

1. VIEWS ARE NOT TO SCALE: USE DIMENSIONS AND TABLE.

[†] Reference Application Note S2083 for lead-free solder reflow recommendations. Plating is 100% matte tin over copper.

XR1011-QH



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4.5 - 10.5 GHz
Rev. V2

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